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List of articles citing

Hole injection and efficiency droop improvement in InGaN/GaN light-emitting diodes by band-engineered electron blocking layer

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#	Paper	IF	Citations
180	Theoretical study of polarization-doped GaN-based light-emitting diodes. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 101110	3.4	49
179	Numerical investigation on the enhanced carrier collection efficiency of Ga-face GaN/InGaN p-i-n solar cells with polarization compensation interlayers. <b>2011</b> , 36, 3500-2		21
178	Study of 375 nm ultraviolet InGaN/AlGaIn light-emitting diodes with heavily Si-doped GaN transition layer in growth mode, internal quantum efficiency, and device performance. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 123102	2.5	5
177	Hole transport improvement in InGaN/GaN light-emitting diodes by graded-composition multiple quantum barriers. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 171106	3.4	114
176	Droop improvement in blue InGaN/GaN multiple quantum well light-emitting diodes with indium graded last barrier. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 233501	3.4	52
175	N-polar III-nitride quantum well light-emitting diodes with polarization-induced doping. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 171104	3.4	55
174	Performance enhancement of blue light-emitting diodes with a special designed AlGaIn/GaN superlattice electron-blocking layer. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 221103	3.4	108
173	Improvement of Performance in p-Side Down InGaN/GaN Light-Emitting Diodes with Graded Electron Blocking Layer. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 080212	1.4	7
172	Improved efficiency droop characteristics in an InGaN/GaN light-emitting diode with a novel designed last barrier structure. <i>Chinese Physics B</i> , <b>2012</b> , 21, 128504	1.2	6
171	Efficiency enhancement of blue InGaN/GaN light-emitting diodes with an AlGaIn-GaN-AlGaIn electron blocking layer. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 094503	2.5	37
170	Experimental determination of current spill-over and its effect on the efficiency droop in InGaN/GaN blue-light-emitting-diodes. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 031905	3.4	41
169	Improvement of characteristics of InGaN-based laser diodes with undoped InGaN upper waveguide layer. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 113105	2.5	18
168	Influence of polarization-matched AlGaInN barriers in blue InGaN light-emitting diodes. <b>2012</b> , 37, 1574-6		16
167	Polarization Matching in AlGaIn-Based Multiple-Quantum-Well Deep Ultraviolet Laser Diodes on AlN Substrates Using Quaternary AlInGaIn Barriers. <b>2012</b> , 30, 3017-3025		6
166	p-InGaIn/AlGaIn electron blocking layer for InGaN/GaN blue light-emitting diodes. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 261106	3.4	27
165	Advantages of GaN based light-emitting diodes with a p-InGaIn hole reservoir layer. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 141106	3.4	69
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160	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 161110	3-4	74
159	Suppression of electron overflow and efficiency droop in N-polar GaN green light emitting diodes. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 111118	3-4	118
158	Improvement of hole injection and electron overflow by a tapered AlGaIn electron blocking layer in InGaIn-based blue laser diodes. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 031105	3-4	37
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144	Polarization doping for III-nitride optoelectronics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2013</b> , 210, 1369-1376	1.6	19
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136	Dependence of InGaN solar cell performance on polarization-induced electric field and carrier lifetime. <i>Chinese Physics B</i> , <b>2013</b> , 22, 098801	1.2	3
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31	Improvement of Light Extraction in Deep Ultraviolet GaN Light Emitting Diodes with Mesh P-Contacts. <i>Applied Sciences (Switzerland)</i> , <b>2020</b> , 10, 5783	2.6	5
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22	Upping the internal quantum efficiency of green light-emitting diodes by employing a graded AlGaIn barrier and an electron blocking layer. <i>IET Optoelectronics</i> , <b>2021</b> , 15, 69-74	1.5	
21	The most optimal barrier height of InGaIn light-emitting diodes. <i>Applied Physics A: Materials Science and Processing</i> , <b>2021</b> , 127, 1	2.6	1
20	Investigation of efficiency droop in InGaIn/GaN-based LEDs with a gradually varying In composition in each InGaIn well layer. <i>Chinese Physics B</i> ,	1.2	0

19	Near-white light-emitting diode from p-CuO/n-GaN heterojunction with an i-CuO electron blocking layer. <i>Journal of Alloys and Compounds</i> , <b>2021</b> , 867, 159145	5.7	8
18	Exploring superlattice DBR effect on a micro-LED as an electron blocking layer. <i>Optics Express</i> , <b>2021</b> , 29, 26255-26264	3.3	3
17	Performance Enhancement of InGaN Light-Emitting Diodes with InGaN/GaN/InGaN Triangular Barriers. <i>ECS Journal of Solid State Science and Technology</i> , <b>2021</b> , 10, 086004	2	
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10	Efficiency Droop of Nitride-Based Light-Emitting Diodes. <i>Series in Optics and Optoelectronics</i> , <b>2017</b> , 99-122		
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2	Theoretical Optical Output Power Improvement of InGaIn-Based Violet Laser Diode Using AlGaIn/GaN Composite Last Quantum Barrier. <b>2022</b> , 12, 3990		1

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